

# A laser-produced plasma extreme ultraviolet (EUV) source by use of liquid microjet target

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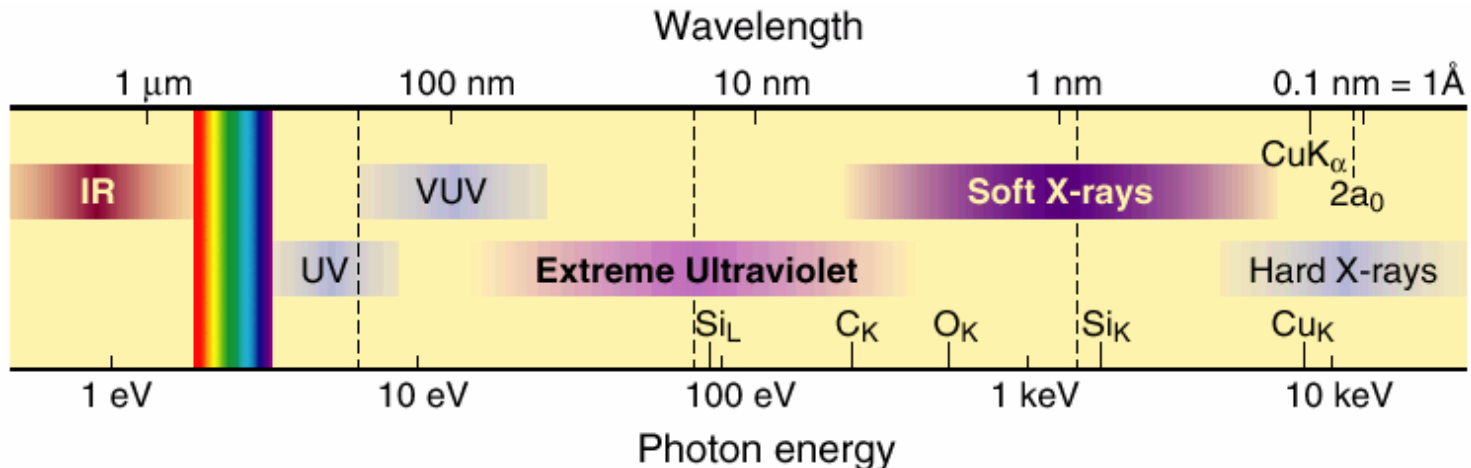
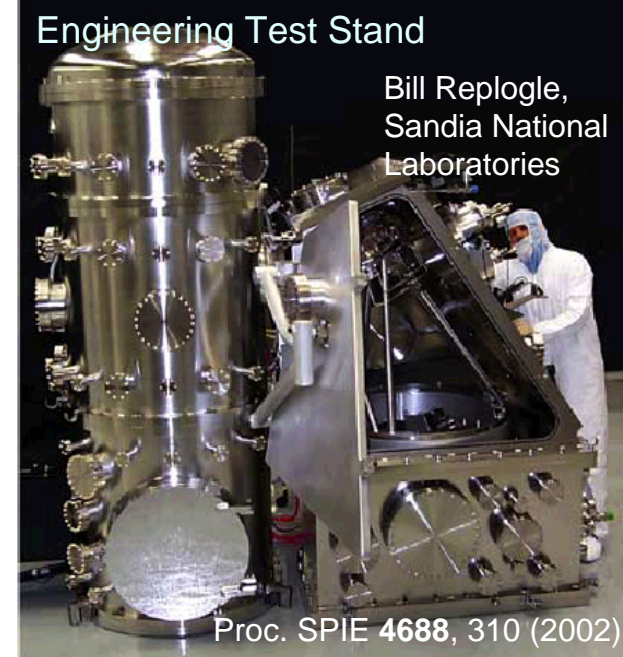


Work supported by MEXT (Ministry of Education, Culture, Science and Technology, Japan) under contract subject "Leading project for EUV lithography source development"

# Background: EUV light source for the next generation lithography

光源	•01	•02	•03	•04	•05	•06	•07	•08	•09	•10
テクノロジーノード	130nm	115nm	100nm	90nm	80nm	70nm	65nm	60nm	50nm	45nm
•KrF	KrF									
•ArF	ArF									
•F2			F2							
•EUV					EUV					

International Technology Roadmap for Semiconductors (ITRS)



# Joint requirements for EUV source: 13.5 nm (2%BW), 115 W, 7-10 kHz

## Joint Requirements for EUV Source

### SOURCE CHARACTERISTICS

### REQUIREMENTS

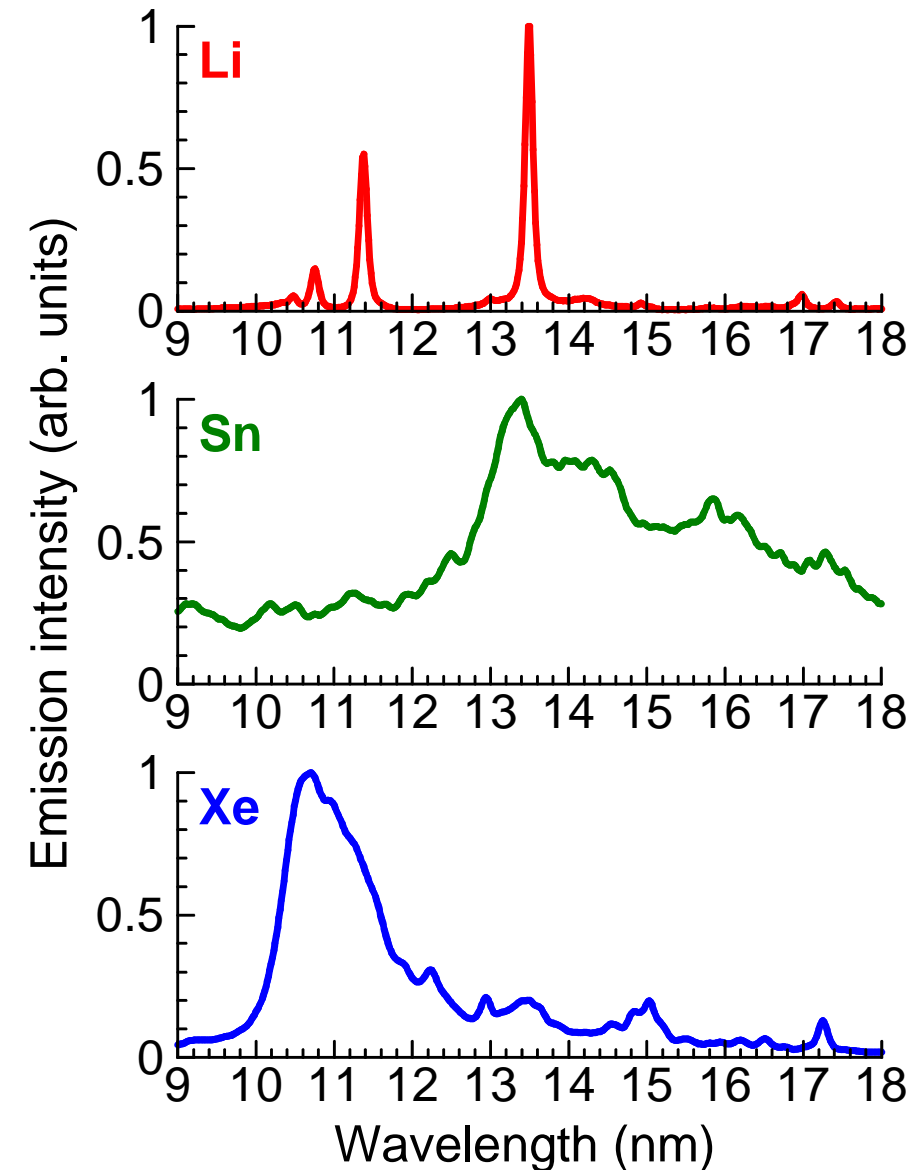
• Wavelength	13.5 (nm)
• EUV Power (in-band)	115 (W) (after intermediate focus)
• Repetition Frequency	> 7 - 10 kHz *
• Integrated Energy Stability	± 0.3% (3σ over 50 pulses)
• Source Cleanliness	≥ 30,000 hours (after intermediate focus)
• Etendue of Source Output	1 – 3.3 mm <sup>2</sup> sr (max)*
• Maximum Solid Angle to Illuminator	0.03 – 0.2 (sr) (depending on particular optical scheme)*
• Spectral Purity	
130 - 400 nm (DUV/VUV)	≤ TBD – 7% (design dependent)*
> 400 nm (Vis/IR)	TBD

\* Not agreed among participants

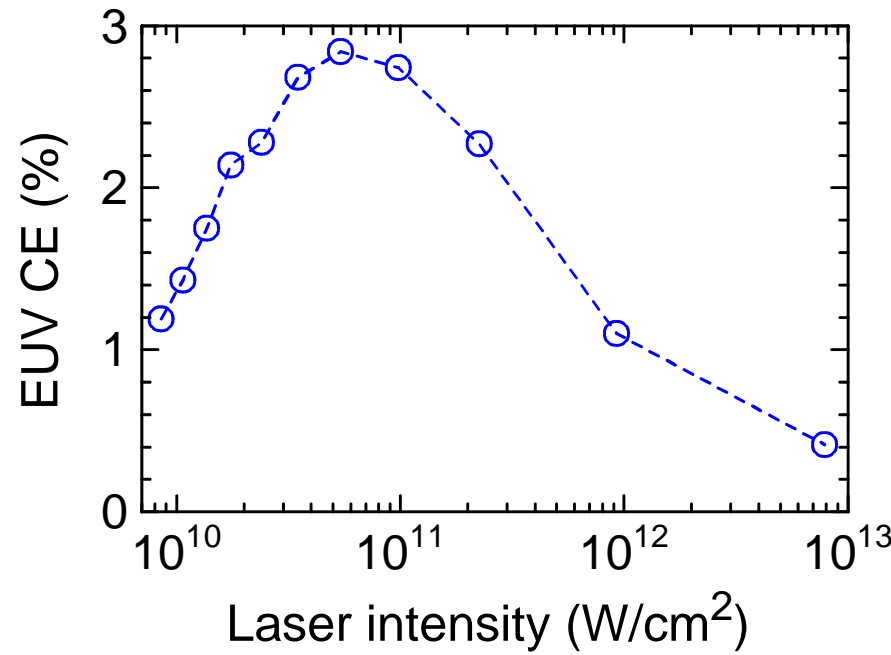
# EUV emission spectra from possible plasma materials



宮崎大学



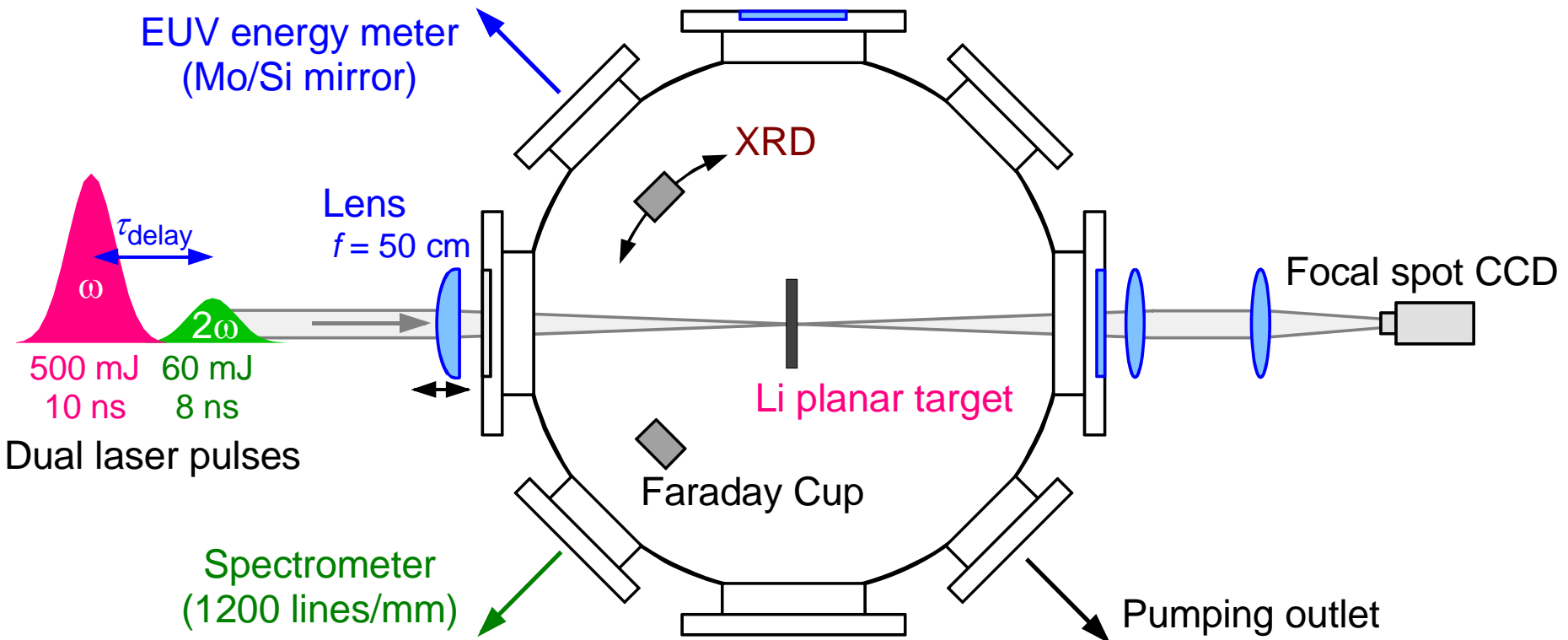
**3<sup>rd</sup> International EUVL Symposium**  
Date : **November 1 - 4, 2004**  
Venue : **Sheraton Grande Ocean Resort Miyazaki, JAPAN**  
Committee : Conference chairperson : Prof. Y. Horiike  
Program committee chairperson : Dr. S. Okazaki  
Deadline of abstract submission : **July 1<sup>st</sup>, 2004**  
URL : [www.euva.or.jp](http://www.euva.or.jp)  
e-mail : [info@euva.or.jp](mailto:info@euva.or.jp)



**"The Optimal Source Path to HVM"**  
D. Myers, B. Llène, I. Fomenkov,  
B. Hansson, and B. Bolliger (CYMER)

# Schematic diagram of experimental setup using planar Li target

Wavelength: 1064 nm  
Laser energy : < 1.4 J  
Pulse width: 10 ns (FWHM)  
Spot size: 300  $\mu\text{m}\phi$





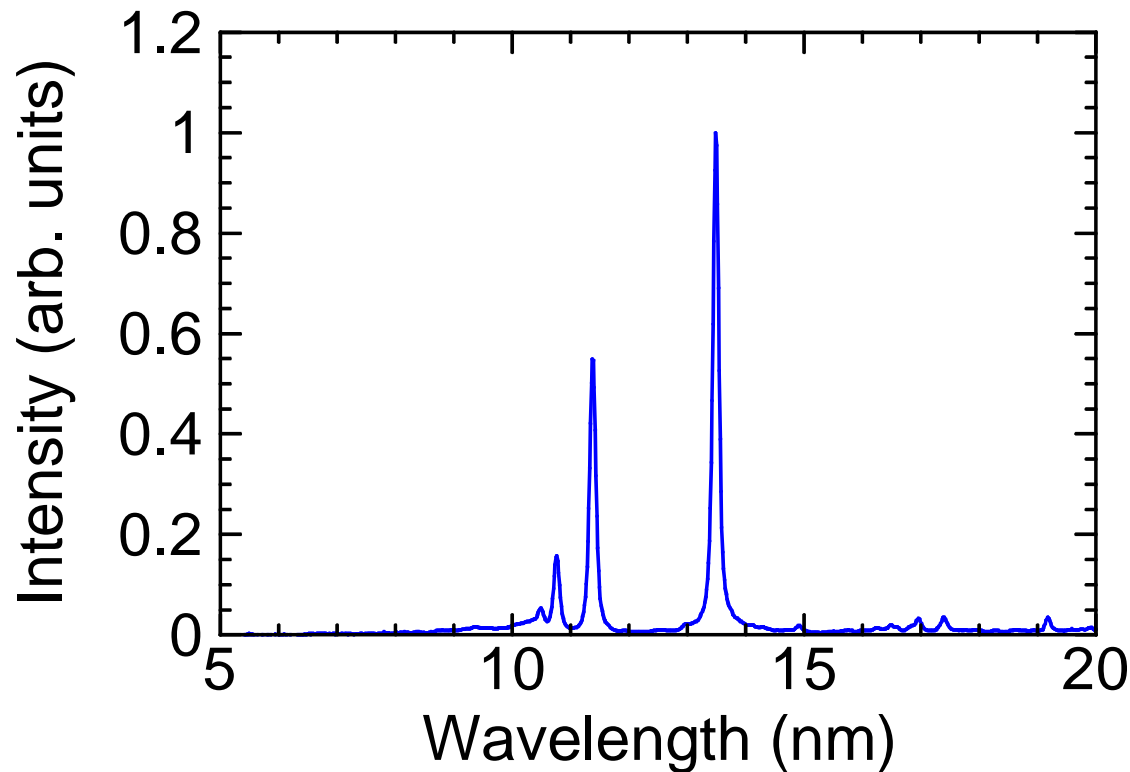
# EUV spectrum of a laser-produced lithium plasma

Laser intensity:  $7 \times 10^{10} \text{ W/cm}^2$

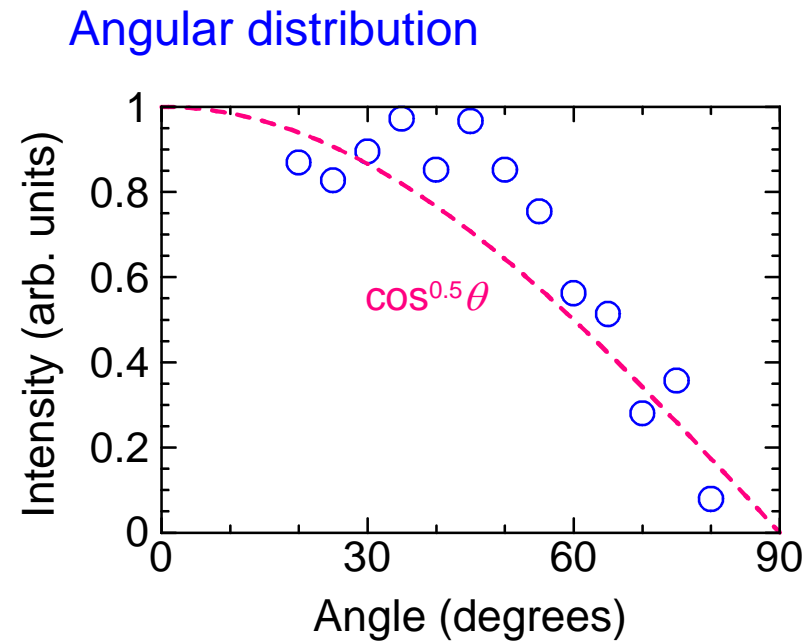
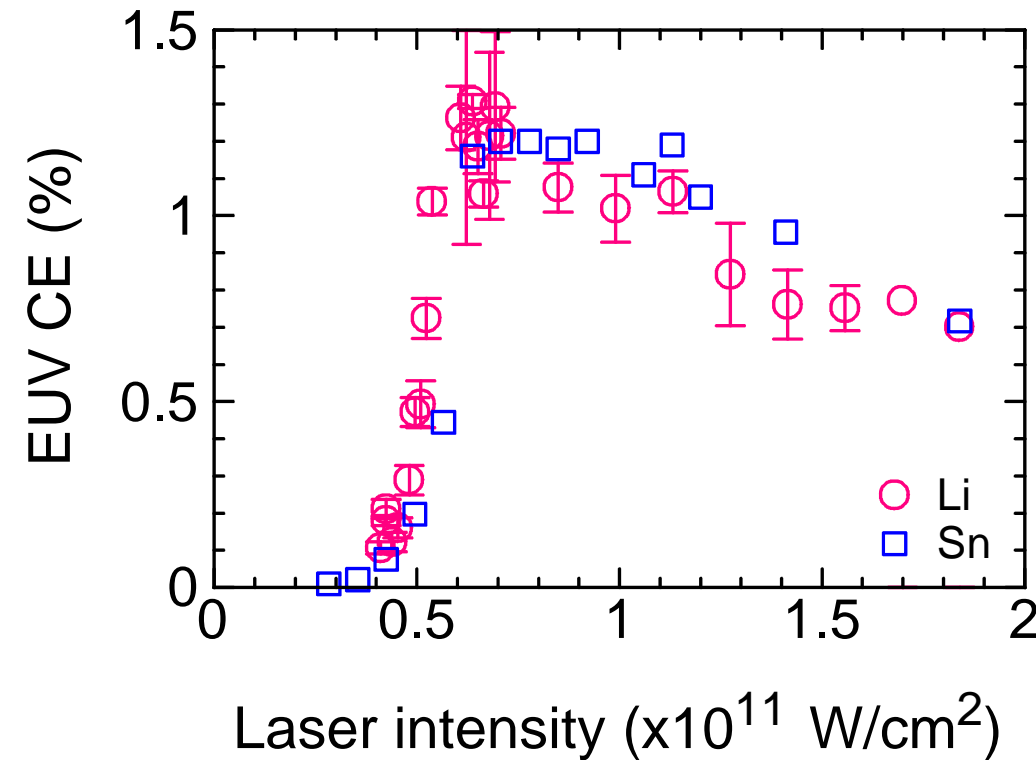
Laser energy : 500 mJ

Pulse width: 10 ns (FWHM)

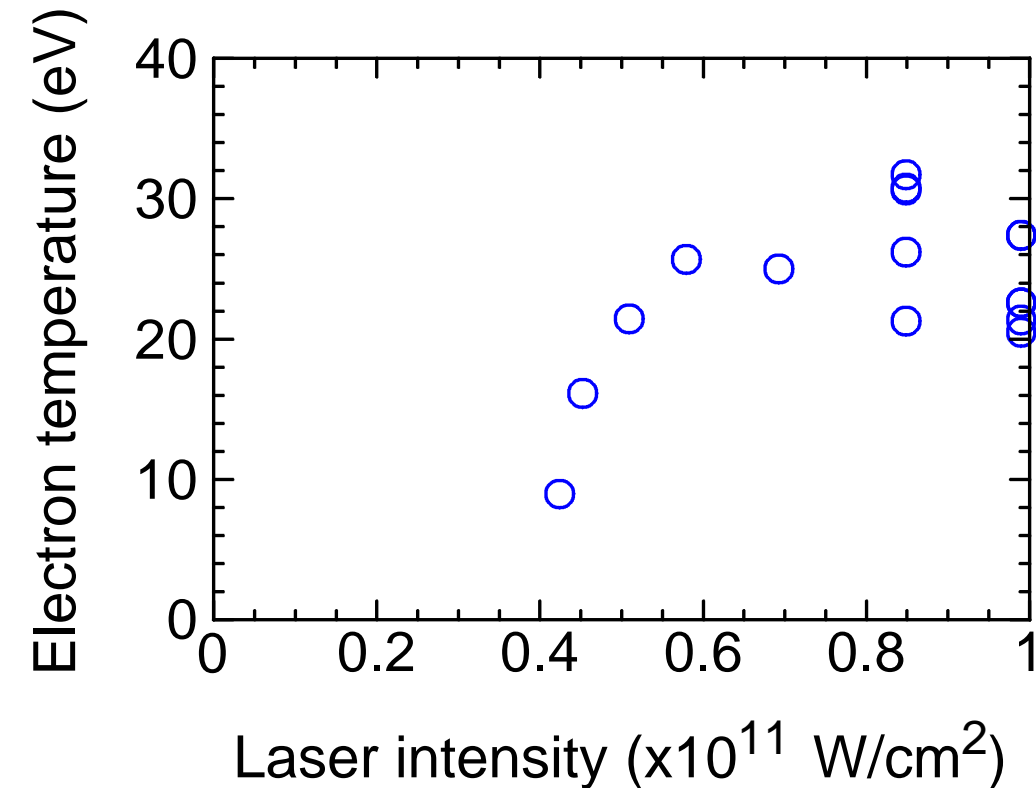
Spot size:  $300 \mu\text{m}\phi$



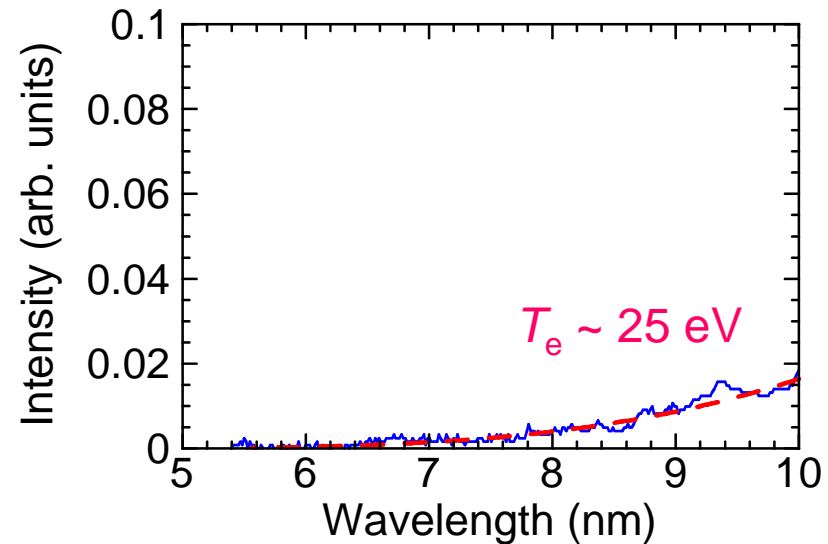
# Laser intensity dependence of EUV CE using a single laser pulse



# Estimation of an electron temperature using bound-free transitions in $\text{Li}^{2+}$ ions



Emission due to bound-free transitions



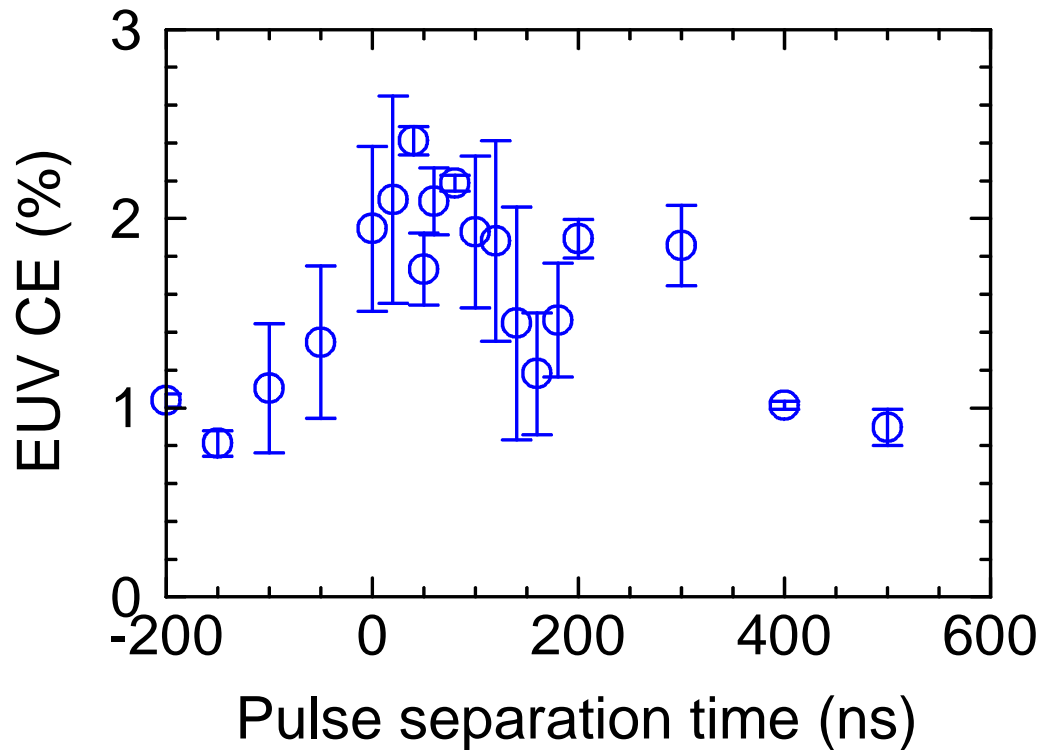


# Pulse separation time dependence of EUV CE utilizing dual laser pulses

Pre-pulse: 532 nm, 60 mJ, 8 ns ( $< 2 \times 10^{10}$  W/cm<sup>2</sup>)

Main pulse: 1064 nm, 500 mJ, 10 ns, 300  $\mu$ m ( $7 \times 10^{10}$  W/cm<sup>2</sup>)

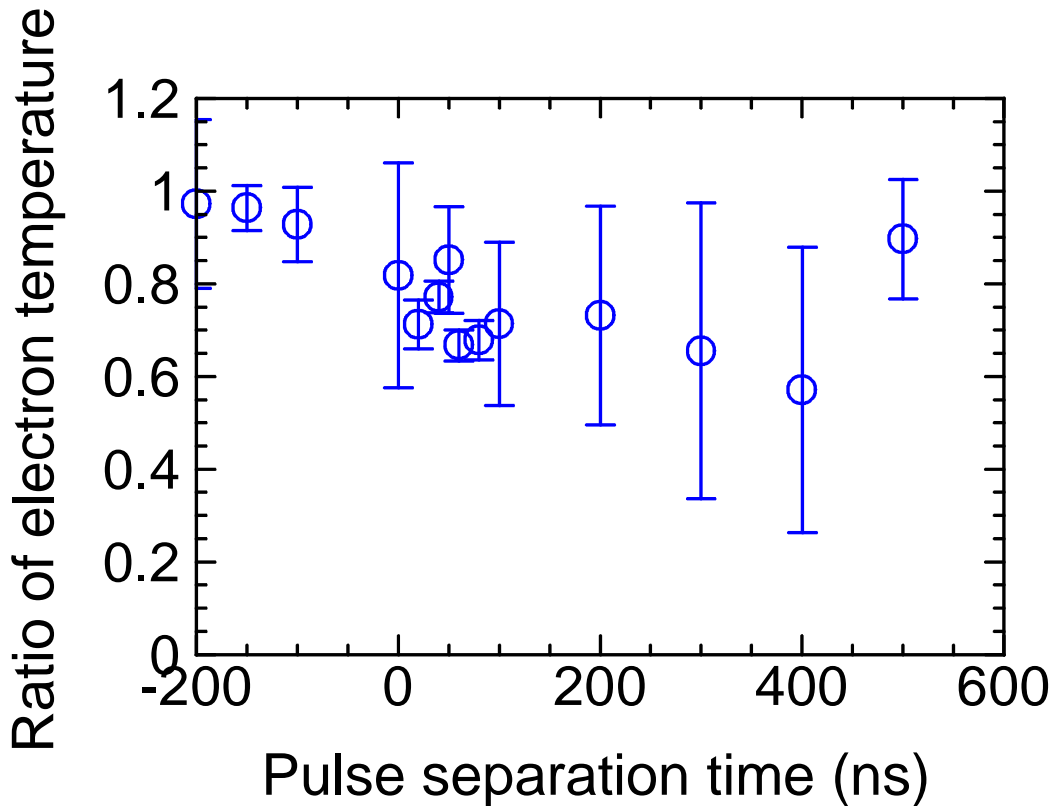
Optimum delay separation time: 20-50 ns



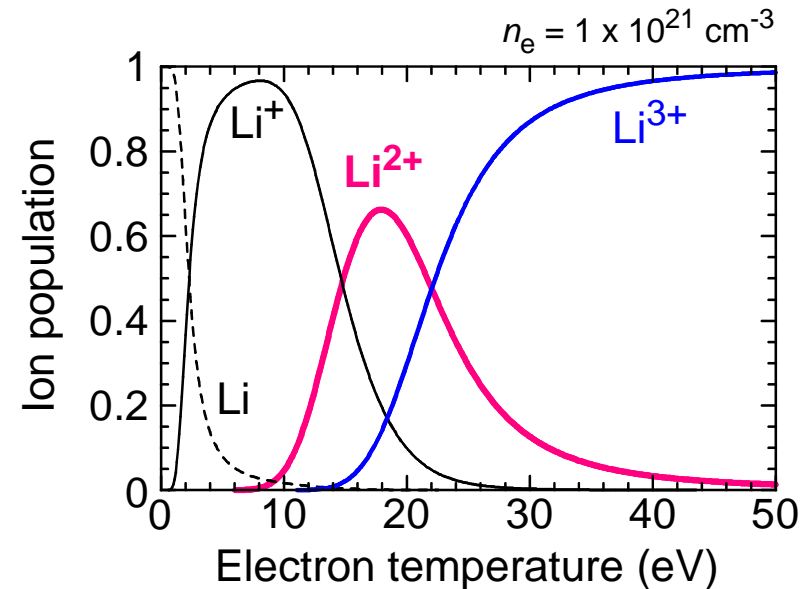
# Ratio of electron temperature as a function of pulse separation time

Pre-pulse: 532 nm, 60 mJ, 8 ns ( $< 2 \times 10^{10}$  W/cm<sup>2</sup>)

Main pulse: 1064 nm, 500 mJ, 10 ns, 300  $\mu$ m ( $7 \times 10^{10}$  W/cm<sup>2</sup>)



CR model





Objective:

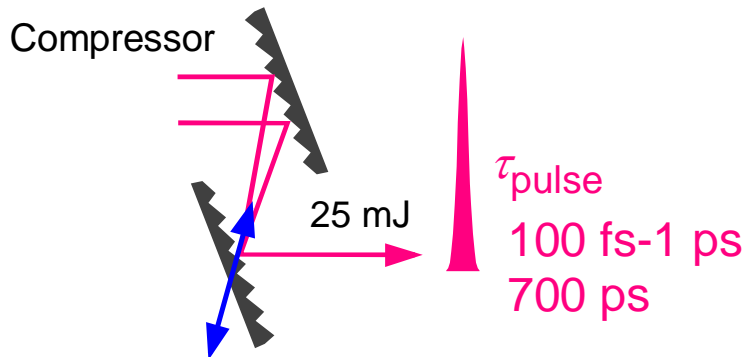
Enhancement of the EUV CE

- Enhancement of the EUV CE by use of *dual* laser pulses
  - Plasma hydrodynamics of a Li plasma should be regulated.
  - Optimum Li plasma parameters could thus be realized.

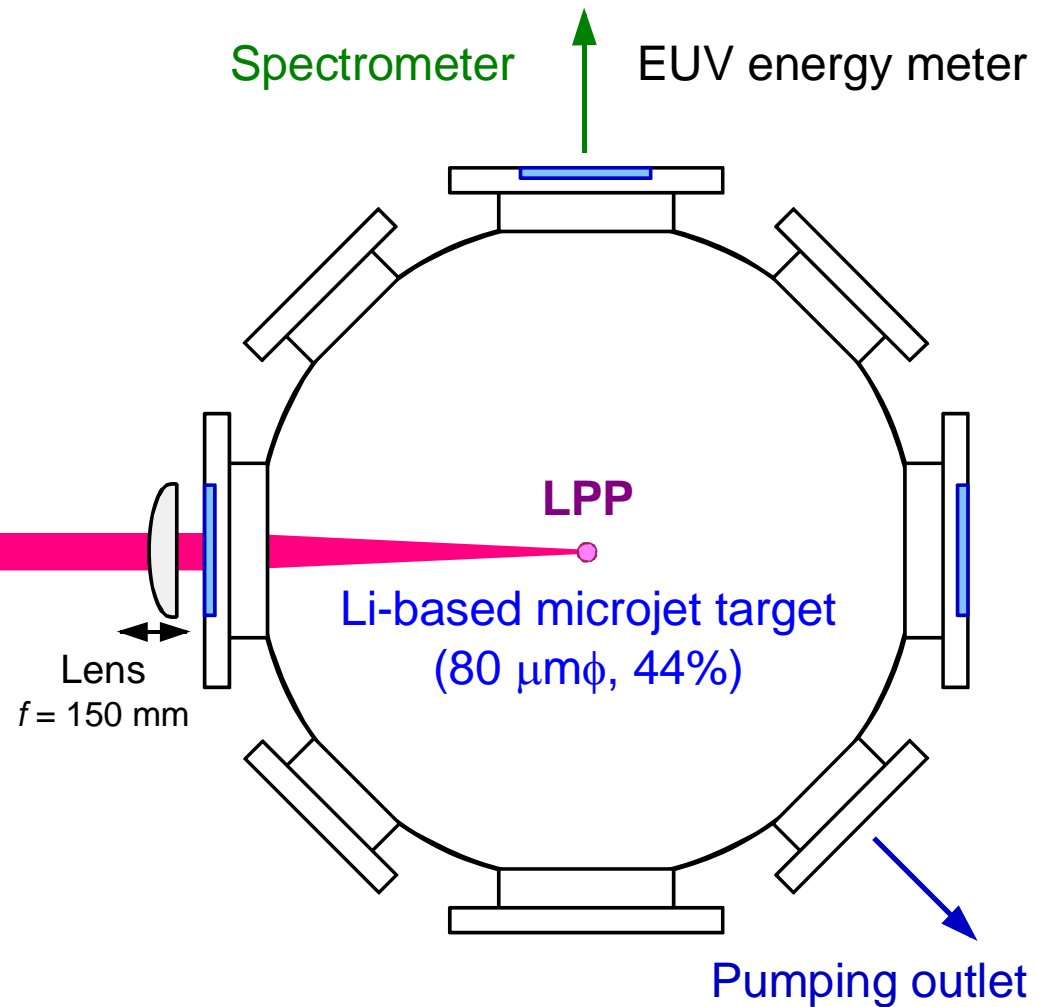
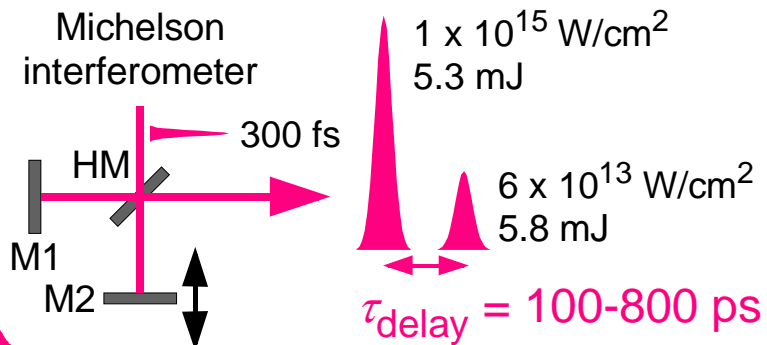
# Experimental setup using ultrashort, high-intensity laser pulses

## Ti:Sapphire laser pulse

### Adjustable pulse width



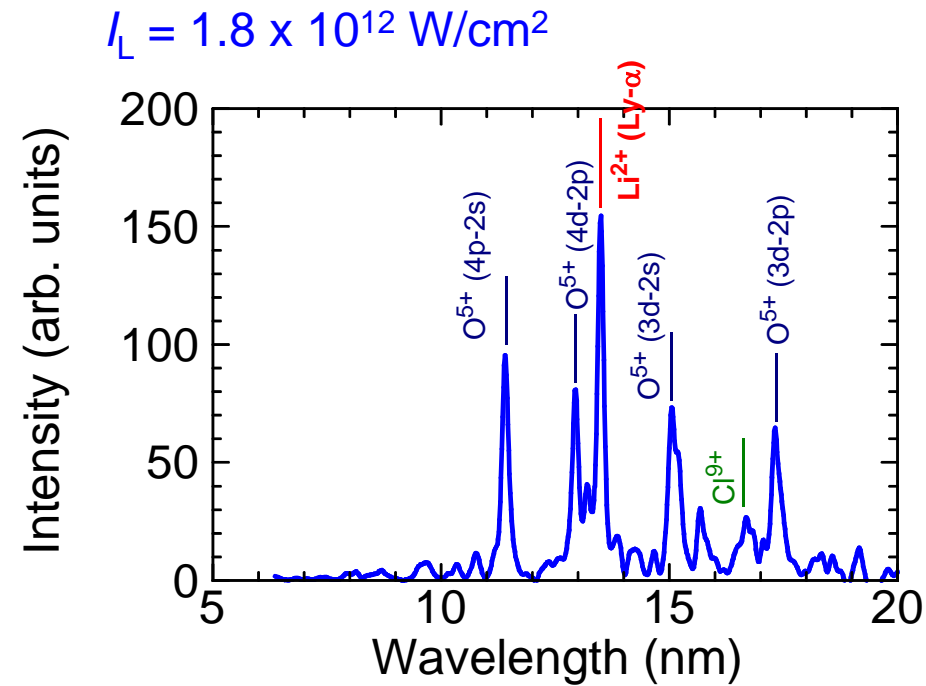
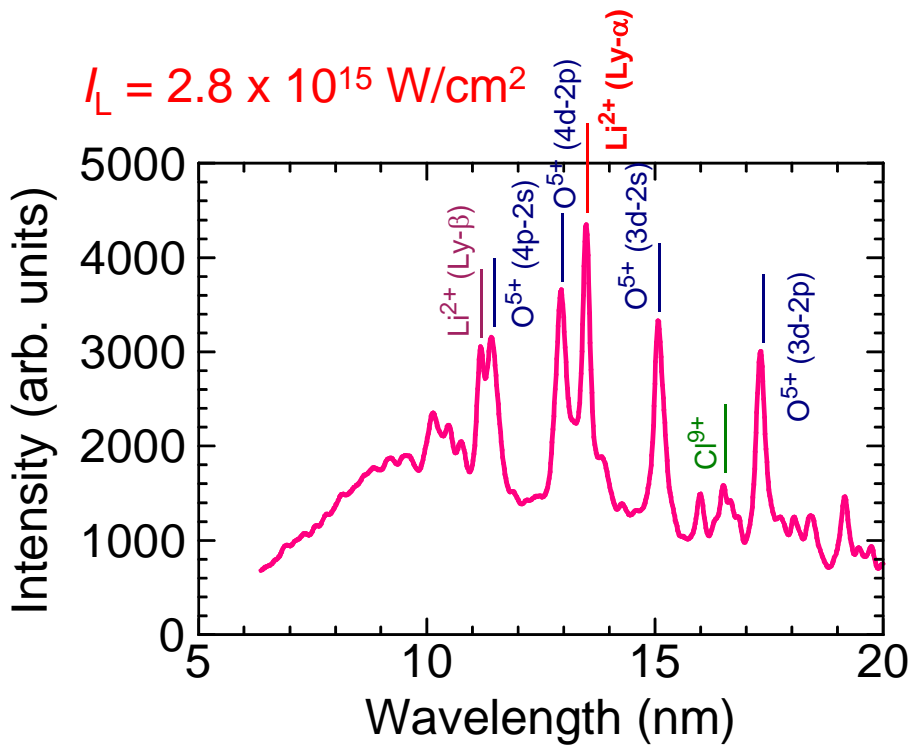
### Adjustable separation time



# EUV spectra from a Li-contained plasma at different laser intensities



Li concentration (by mass): 44.4%  
Jet diameter: 80  $\mu\text{m}\phi$   
Laser energy: 25 mJ

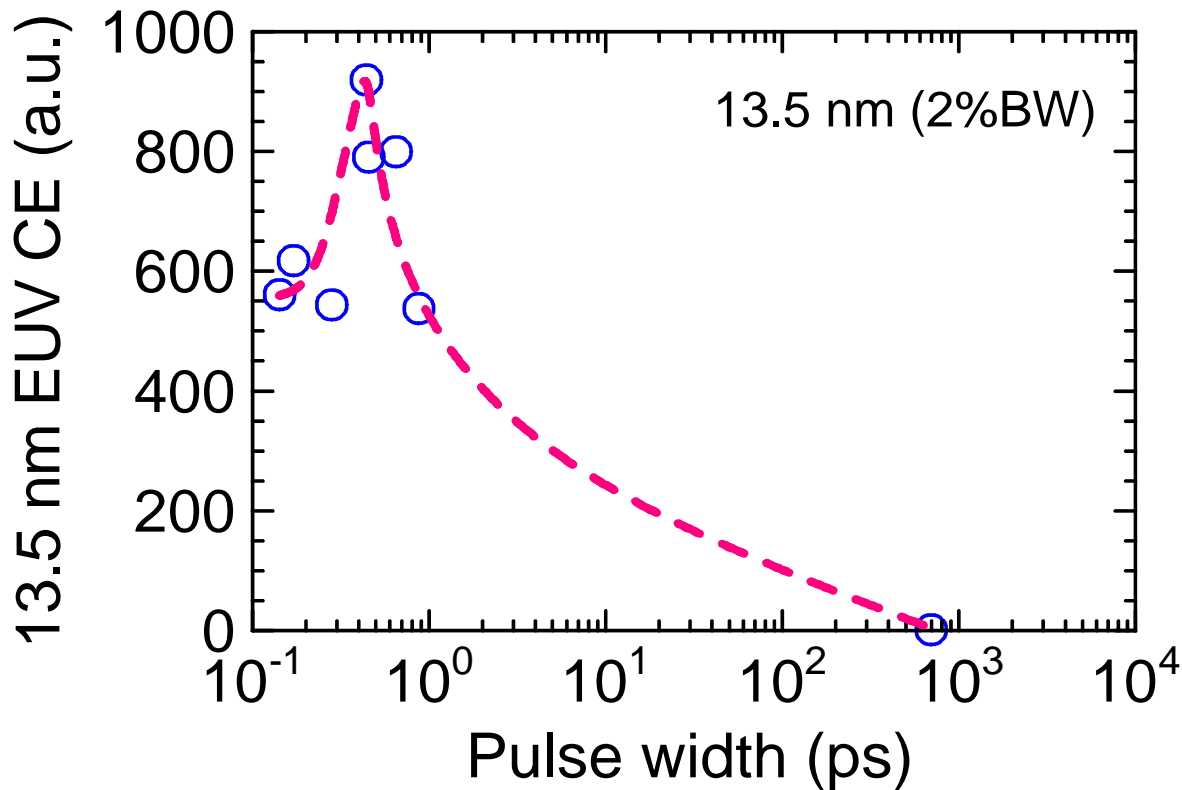


# Subpicosecond pulse width dependence of the EUV CE

Li concentration (by mass): 44.4%

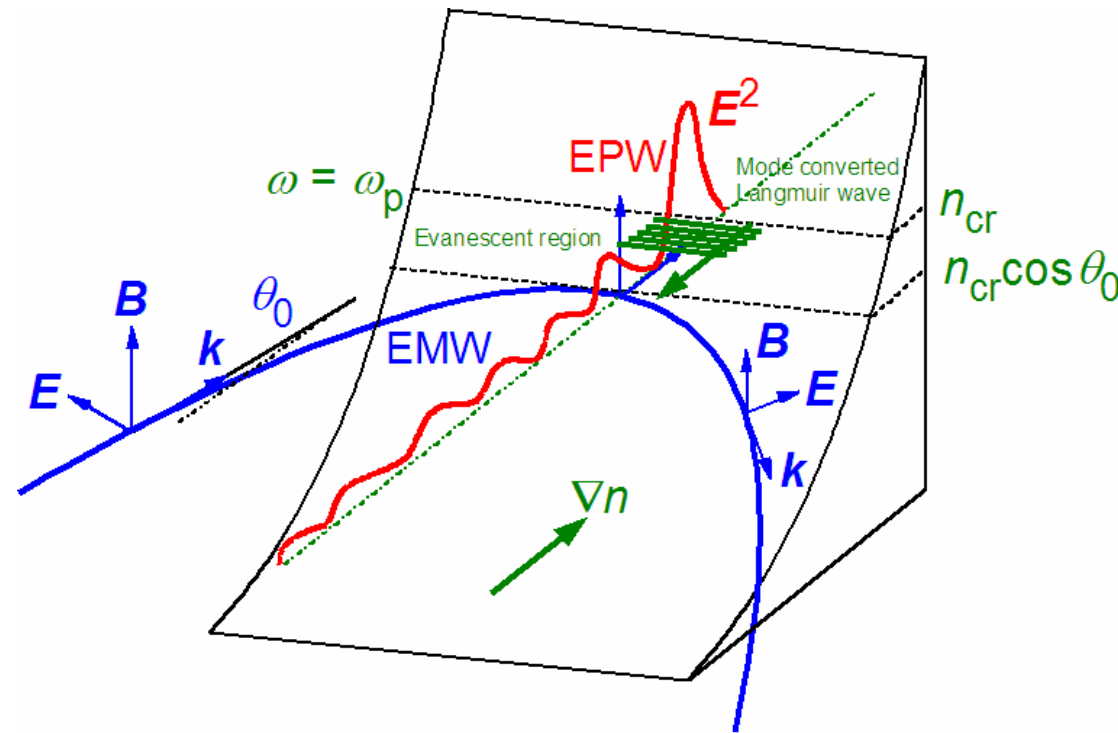
Jet diameter: 80  $\mu\text{m}\phi$

Laser energy: 25 mJ



# Optimum pulse width explained by the resonant absorption process

Resonant absorption is dominant in a steepened density profile.



Absorption thickness

$$L_{cr} = L_{opt} \approx \frac{3\sqrt{3}}{8k \cos^3 \theta}$$

$$L_{opt} \approx c_S \tau_{pulse}$$

$$c_S \approx 2 \times 10^7 \text{ cm/s,}$$

$$\lambda = 2\pi/k = 0.8 \text{ } \mu\text{m,}$$

$$L_{opt} \approx 82 \text{ nm for } \theta = 0$$

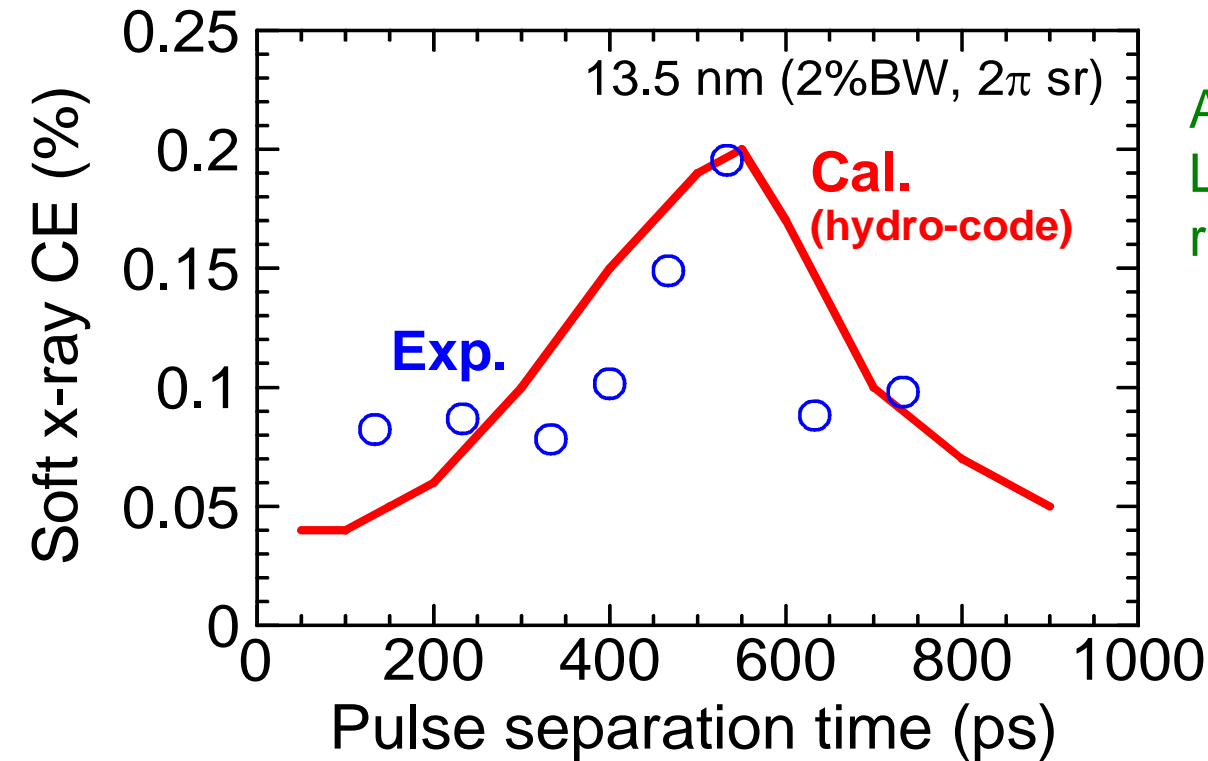
$$\tau_{pulse} \approx 400 \text{ fs}$$

[1] C. Garban-Labaune, E. Fabre, C. E. Max, R. Fabbro, F. Amiranoff, J. Virmont, M. Weinfeld, A. Michard, Phys. Rev. Lett. **48**, 1018 (1982).

[2] V. L. Ginzburg, "Propagation of Electromagnetic Waves in Plasmas" (Pergamon, New York, 1970).

[3] E. Parra, I. Alexeev, J. Fan, K. Y. Kim, S. J. McNaught, and H. M. Milchberg, Phys. Rev. E **62**, R5931 (2000).

# Enhancement of the EUV CE by use of dual subpicosecond laser pulses

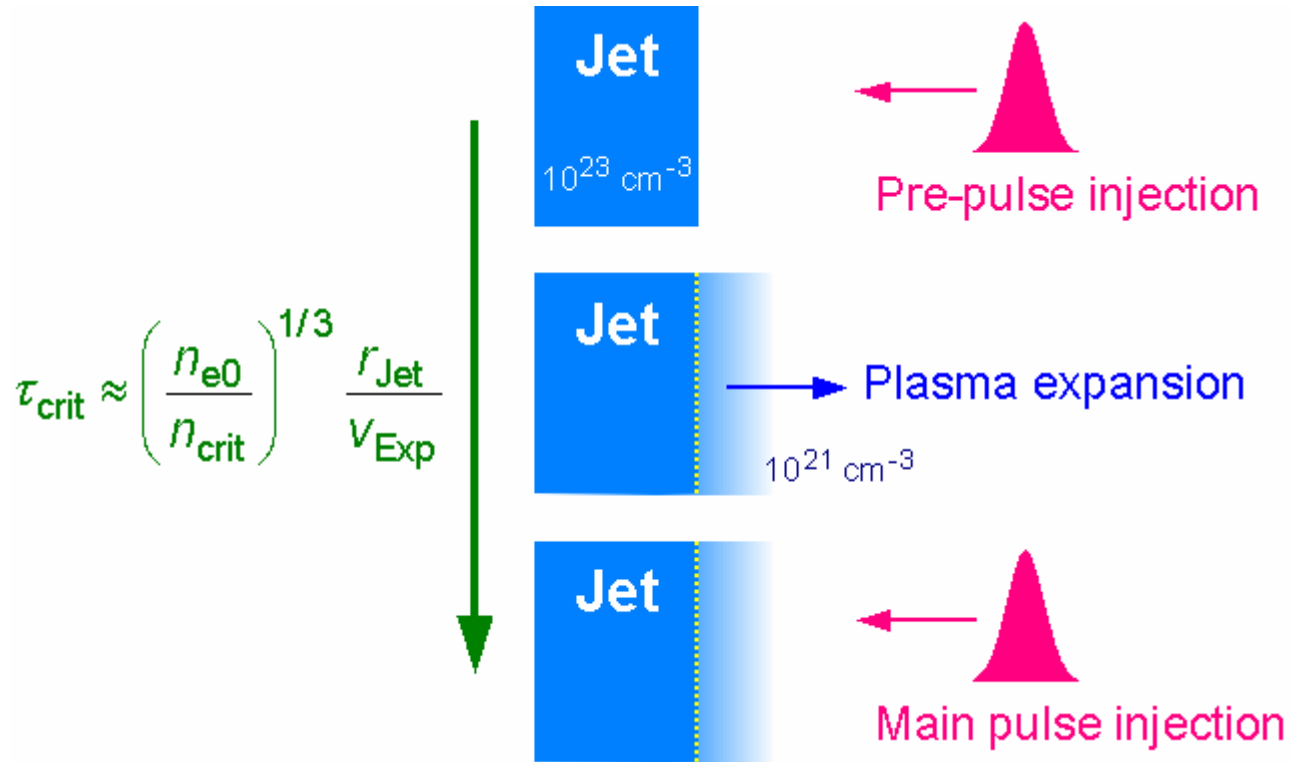


A one-fluid two-temperature Lagrangian code well reproduced the experiments.

- Plasma hydrodynamic
- Atomic code
- Plasma emission



# Optimum delay time explained by the plasma expansion (simpler estimate)

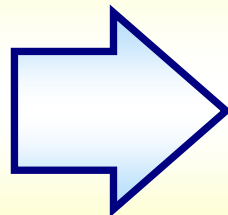


$$n_{e0} = 10^{22} - 10^{23} \text{ cm}^{-3}$$

$$n_{\text{crit}} = 1.7 \times 10^{21} \text{ cm}^{-3}$$

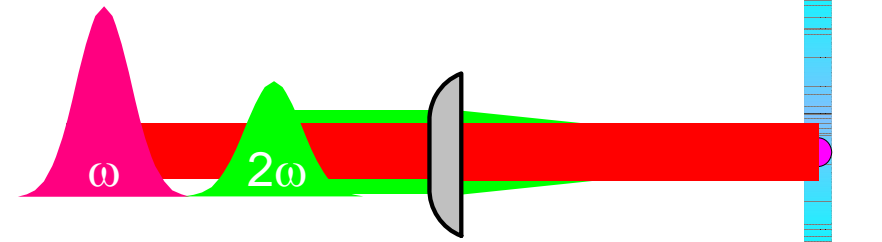
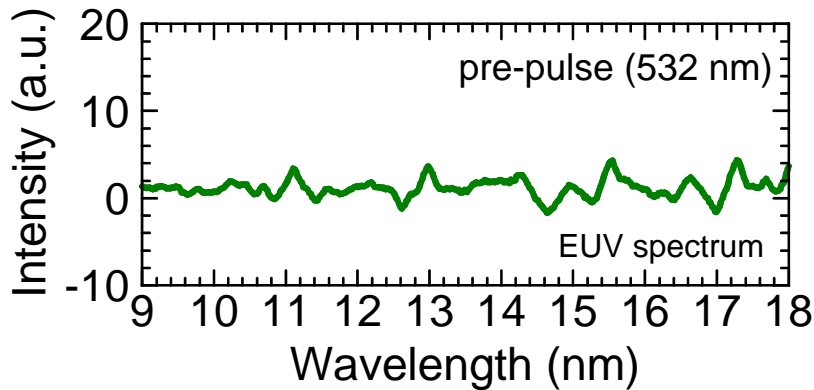
$$r_{\text{Jet}} = 40 \text{ } \mu\text{m} \quad (2r_{\text{Jet}} = 80 \text{ } \mu\text{m})$$

$$V_{\text{exp}} \approx c_s \approx 2 \times 10^7 \text{ cm/s}$$

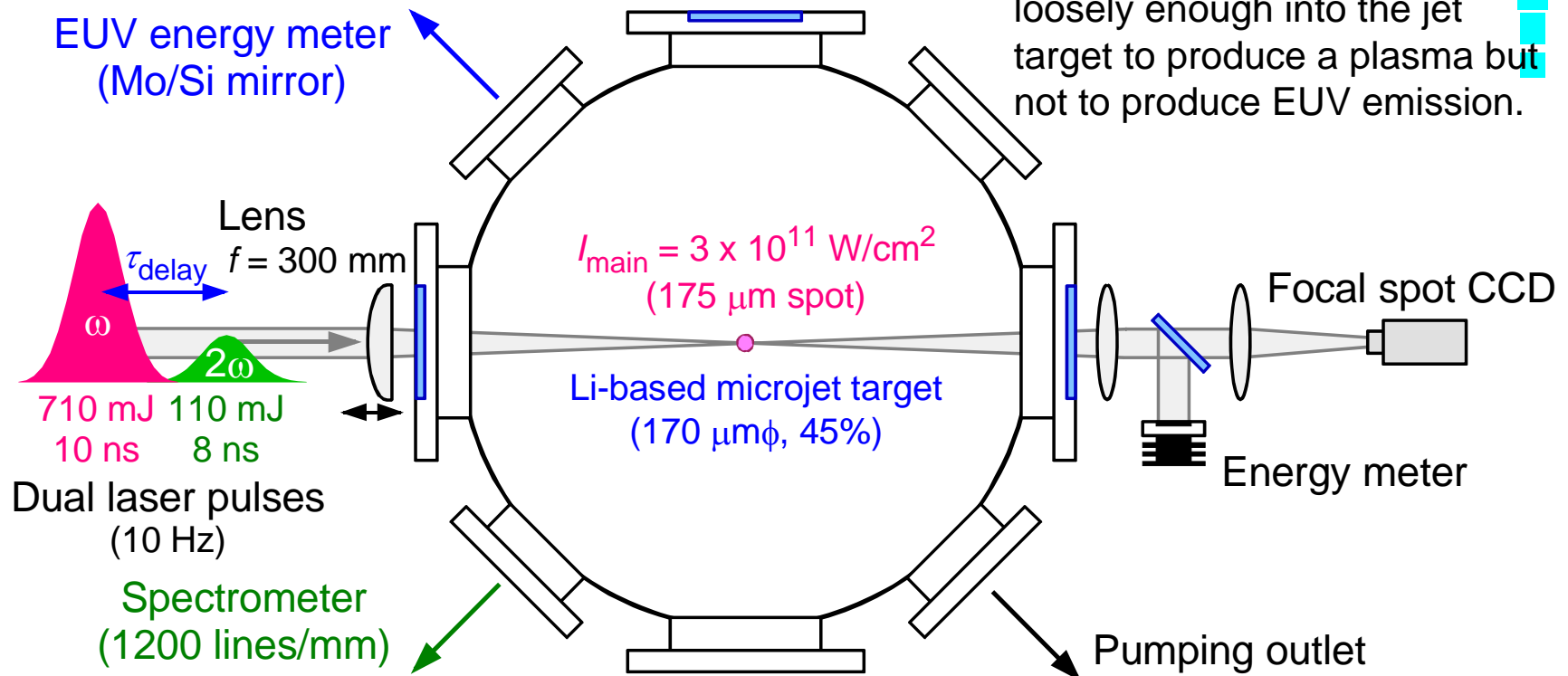


$$\tau_{\text{exp}} \approx 400 \text{ ps}$$

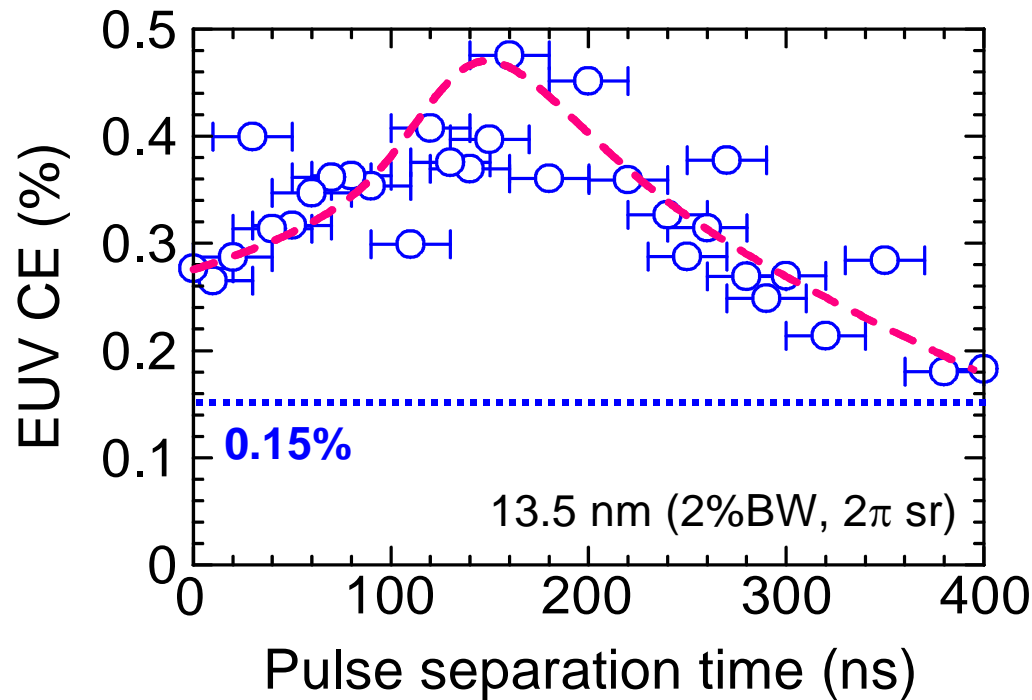
# Experimental setup using dual nanosecond laser pulses



A  $2\omega$  prepulse was focused loosely enough into the jet target to produce a plasma but not to produce EUV emission.

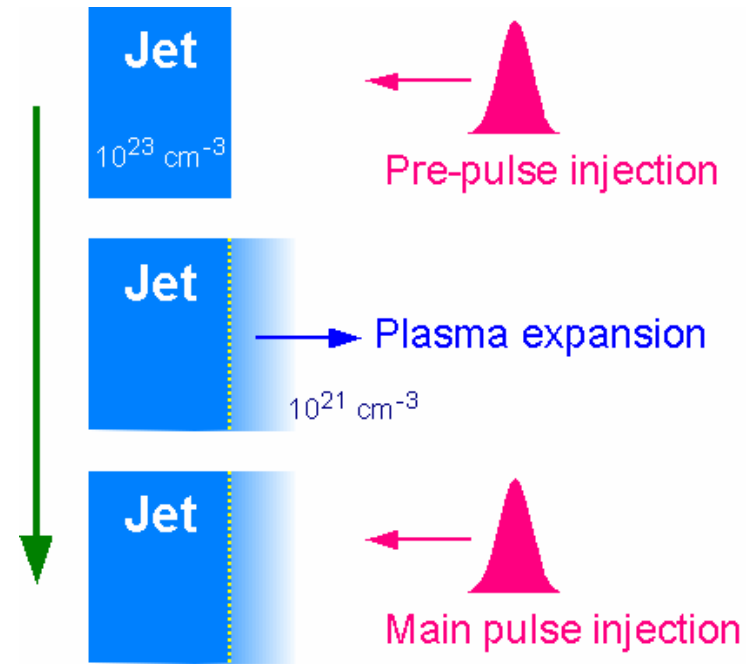


# Enhancement of the EUV CE by use of dual nanosecond laser pulses



A plasma expansion time to its critical density was responsible for the optimal pulse separation time.

APB 80, 409 (2005).



$$\tau_{\text{crit}} \approx \left( \frac{n_{e0}}{n_{\text{crit}}} \right)^{1/3} \frac{r_{\text{Jet}}}{V_{\text{Exp}}} \approx 80 \text{ ns}$$

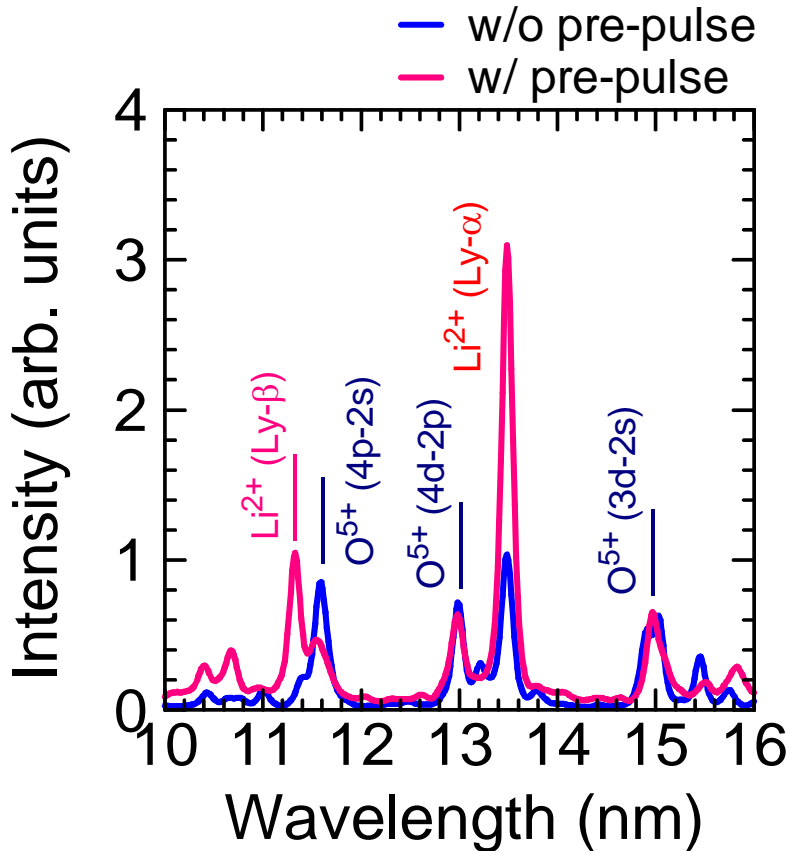
$$n_{e0} = 10^{23} \text{ cm}^{-3}$$

$$n_{\text{crit}} = 10^{21} \text{ cm}^{-3} @ \lambda_L = 1 \mu\text{m}$$

$$2r_{\text{Jet}} = 170 \mu\text{m}$$

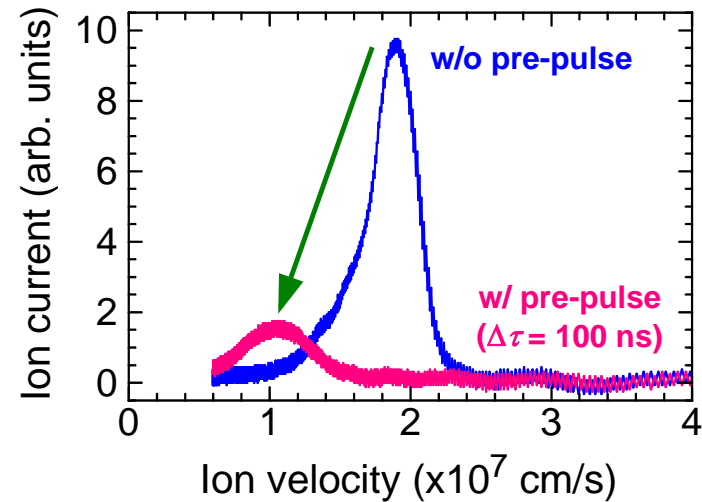
$$V_{\text{Exp}} = 5 \times 10^5 \text{ cm/s} @ 10^{21} \text{ cm}^{-3}$$

# Optimum plasma conditions obtained for the Lyman- $\alpha$ emission at 13.5 nm

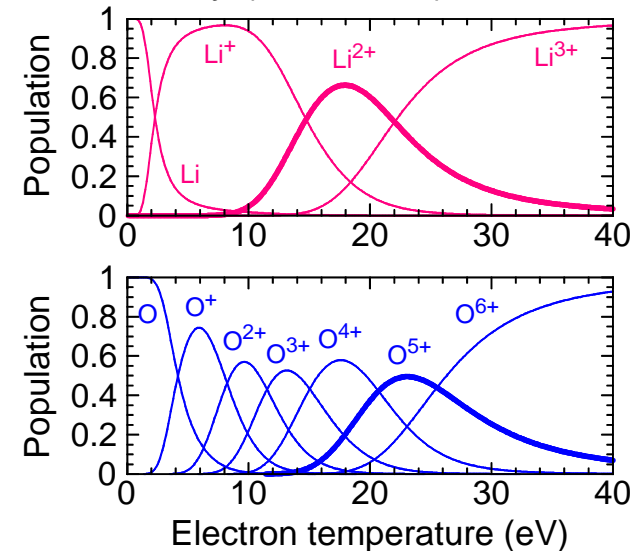


Optimum dual laser parameters produced a plasma where Li 13.5 nm emission became dominant.

APB **80**, 409 (2005).



CR model



■  $\text{Li}^{2+}$  (13.5 nm) population:  $T_e \approx 18$  eV  
■  $\text{O}^{5+}$  (13.0 nm) population:  $T_e \approx 25$  eV



# Summary

- Optimum dual laser parameters for the EUV CE enhancement
  - Subpicosecond pulse width dependence revealed the optimal prepulse width of 400 fs, which corresponded to resonance absorption time of a short scale-length plasma.
  - Dual laser pulse irradiation increased the in-band EUV CE from 0.08% to 0.2% for subpicosecond laser pulses, and from 0.15% to 0.5% for nanosecond laser pulses.
  - Pulse separation time dependence indicated the optimum time separation of 500 ps and 100 ns for subpicosecond and nanosecond laser pulses, respectively, corresponding to the plasma density decrease to its critical density due to the plasma expansion. The difference of the optimum delay time is mainly due to the difference of the plasma expansion velocities determined by different laser intensities.